

**Form PTO-1449**

**INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION**

(Use several sheets if necessary)

Doctor Number (Specie)

Accident Nurses

CS-03-021

10/688, 047

*Apprenti*

Chung Foong Tam et al.

Filing Date

10/17/03

## U. S. PATENT DOCUMENTS

| EXAMINER<br>SEARCHER | DOCUMENT NUMBER | DATE   | NAME               | CLASS | SUBCLASS | ALMO DATE<br>IF APPROPRIATE |
|----------------------|-----------------|--------|--------------------|-------|----------|-----------------------------|
| MG                   | 65418294        | 4/1/03 | Nishio hara et al. | 257   | 402      | 12/1/00                     |
| MG                   | 65148862        | 4/1/03 | U'Ren              | 438   | 791      | 9/22/00                     |

## FOREIGN PATENT DOCUMENTS

**OTHER DOCUMENTS** (including Author, Title, Date, Portion or Pages, Etc.)

|    |   |
|----|---|
|    | - "Optimum Halo Structure for Sub-0.1 μm CMOS FET's", Wan-Kuan<br>Yeh et al., <u>IEEE Transaction Electron Devices</u> , Vol. 48, No. 10,<br>Oct. 2001, pp. 2357 - 2362.                          |
| MG | "Antimony Assisted Arsenic S/D Extension Engineering for<br>Sub-0.1 μm nMOSFETs: A Novel Approach to Steep and Retrograde<br>Indium Pocket Profiles," Howard C.H. Wang et al., <u>IEDM 2001</u> . |
| MG |   |

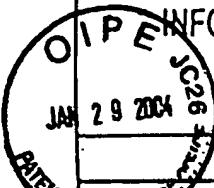
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Maria Guenaro

4-12-05

**EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.



Form PTO-1449

**INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION**

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29 DEC

(Use several shovels if necessary)

**Double Number (Options)**

CS-03-021

Appleton Museum

10 | 688,047

Logon!

"Chung Foong Tan et al.

Filing Date

10/17/03

Group Art Unit

## U. S. PATENT DOCUMENTS

## FOREIGN PATENT DOCUMENTS

**OTHER DOCUMENTS** (including Author, Title, Date, Portions Pages, Etc.)

- "Effects of end-of-range dislocation loops on transient enhanced diffusion of indium implanted in silicon," T. Noda et al., Journal of Applied Physics, Vol. 88, No. 9, Nov. 2001, pp. 4980-4984.

- "Enhanced electrical activation of indium coimplanted with carbon in a silicon substrate," H. Bondarenko et al., Journal of Applied Physics, Vol. 86, No. 10, pp. 5909-5911, Nov. 15, 1999.

Dynamic

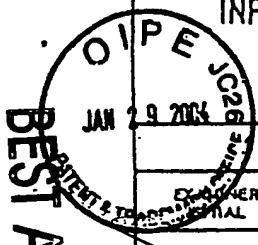
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Form PTO-1449

**INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION**

(Use several sheets if necessary)

Doctor Number (Optional)

CS-03-021

Appleton Museum

10/688,047

Appleton

Chong Peng

100

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#### Organ Art Work

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## U. S. PATENT DOCUMENTS

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## FOREIGN PATENT DOCUMENTS

**OTHER DOCUMENTS** (Including Author, Title, Date, Portion or Pages, Etc.)

|      |   |
|------|---|
| MG - | "Elimination of secondary defects in preamorphized Si by C <sup>+</sup> implantation," Satoshi Michikawa et al., <u>Applied Physics Letters</u> , 62(3), Jan. 1993, pp. 303-305.                            |
| MG - | "Removal of end of range defect in Ge <sup>+</sup> pre-amorphized Si by carbon ion implantation," Peng-Shiu Chen et al., <u>Journal of Applied Physics</u> , Vol. 85, No. 6, March 15, 1999, pp. 3114-3119. |
| MG   |   |
|      |   |

Examiner

DATE COMPLETED

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